

Description

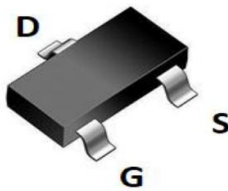
N-channel Enhancement Mode Power MOSFET

Features

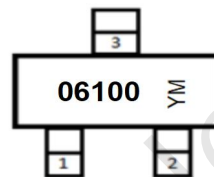
- 60V, 3A
 $R_{DS(ON)}$ Typ = 75m Ω @ V_{GS} = 10V
 $R_{DS(ON)}$ Typ = 85m Ω @ V_{GS} = 4.5V
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free

Applications

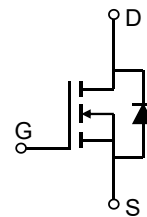
- Load Switch
- PWM Application
- Power Management



SOT-23-3L



Marking and Pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Outline	Package	Reel Size	Reel(pcs)	Per Carton (pcs)
06100	CRMJTL06100A	TAPING	SOT-23-3L	7"	3000	120000

Absolute Maximum Ratings (@ T_J = 25°C unless otherwise specified)

Symbol	Parameter	Value	Units
V_{DS}	Drain-to-Source Voltage	60	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_A = 25^\circ\text{C}$	A
		$T_A = 100^\circ\text{C}$	
I_{DM}	Pulsed Drain Current ⁽¹⁾	12	A
P_D	Power Dissipation	$T_A = 25^\circ\text{C}$	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽²⁾	81	$^\circ\text{C/W}$
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$



Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V	60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 60V, V _{GS} = 0V	-	-	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1.0	1.4	2.0	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽³⁾	V _{GS} = 10V, I _D = 3A	-	75	100	mΩ
		V _{GS} = 4.5V, I _D = 2A	-	85	110	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz	-	350	-	pF
C _{oss}	Output Capacitance		-	29	-	pF
C _{rss}	Reverse Transfer Capacitance		-	23	-	pF
Q _g	Total Gate Charge	V _{GS} = 0 to 10V V _{DS} = 30V, I _D = 3A	-	9	-	nC
Q _{gs}	Gate Source Charge		-	1.5	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	2	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = 10V, V _{DD} = 30V I _D = 2A, R _{GEN} = 3Ω	-	5	-	ns
t _r	Turn-On Rise Time		-	7	-	ns
t _{d(off)}	Turn-Off DelayTime		-	37	-	ns
t _f	Turn-Off Fall Time		-	22	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	3	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	12	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = 3A	-	-	1.2	V

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. $R_{\theta JA}$ is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB
 3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Test Circuit

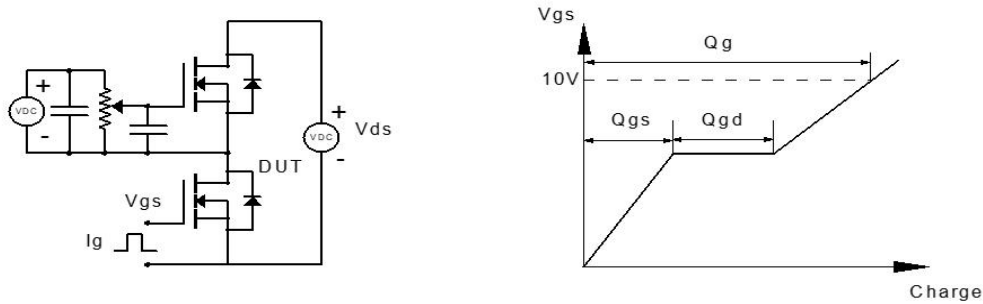


Figure 1: Gate Charge Test Circuit & Waveform

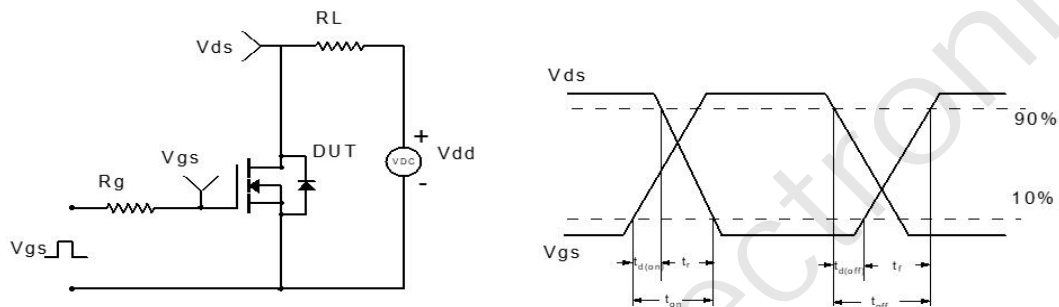


Figure 2: Resistive Switching Test Circuit & Waveform

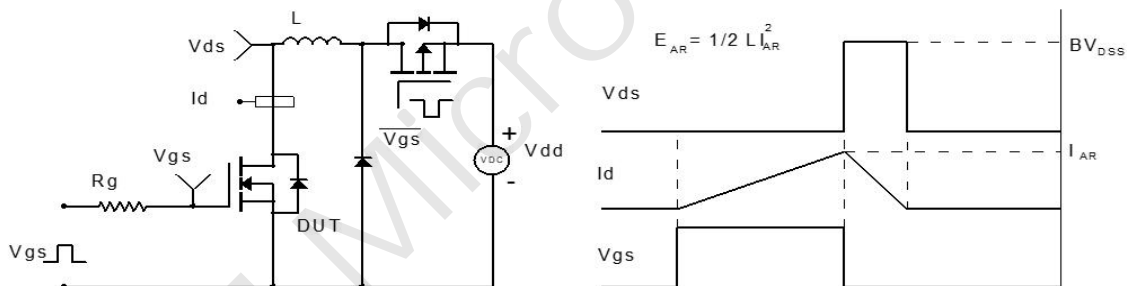


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

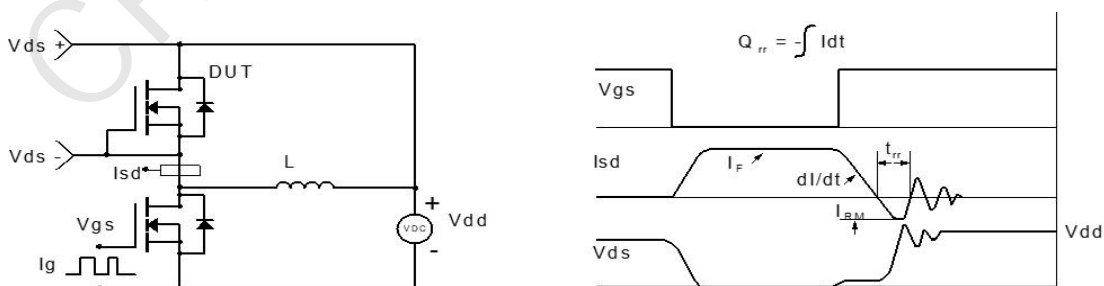
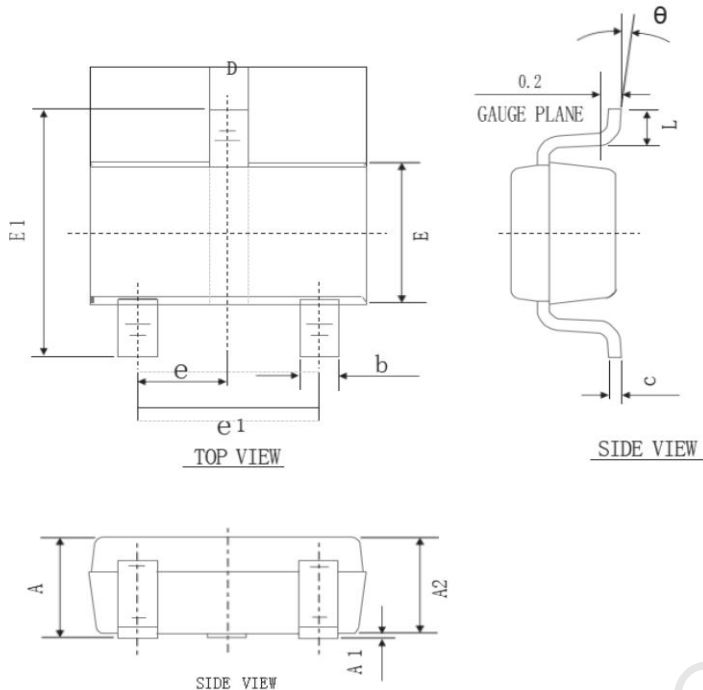


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(SOT-23-3L)



COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A			1.30
A1	0.00	0.05	0.10
A2	1.00	1.10	1.20
b	0.30	0.40	0.50
c	0.10	0.125	0.15
e1	1.80	1.90	2.00
D	2.80	2.90	3.00
E	1.50	1.60	1.70
E1	2.60	2.80	3.00
L	0.30	0.45	0.60
θ	0°	4°	8°
e	0.95BSC		

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